

# S4D065V025S SiC Schottky Diode

#### Features:

- 650V Schottky Diode
- Zero Reverse Recovery Current
- High Frequency Operation
- Positive Temperature Coefficient

Switch Mode Power Supply

AC/DC converters

Booster diodes in PFC, DC/DC

• Temperature independent Switching

**Applications:** 

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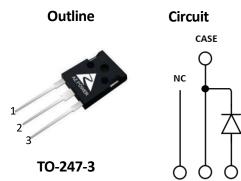
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## **Benefits:**

- Unipolar Rectifier
- Minimal switching loss
- Higher Efficiency
- Low cooling requirement

Symbol	Value	Unit
V <sub>RRM</sub>	650	V
I <sub>F</sub> (Tc=144ºC)	25	А
Q <sub>C</sub>	68	nC



#### **Maximum Ratings**

Symbol	Parameter	Value	Unit	Test Conditions
V <sub>R</sub>	DC Peak Reverse Voltage	650	V	T <sub>J</sub> =25°C
V <sub>RRM</sub>	Repetitive Peak Reverse Voltage	650	V	T <sub>J</sub> =25°C
V <sub>RSM</sub>	Surge Peak Reverse Voltage	650	V	T <sub>J</sub> =25°C
IF	Continuous Forward Current	66 29 25	A	T <sub>c</sub> =25°C T <sub>c</sub> =135°C T <sub>c</sub> =144°C
I <sub>FRM</sub>	Repetitive Peak Forward Surge Current	176 160	А	$T_c$ =25°C, $T_P$ =10ms, Half Sine Wave Tc=125°C, $T_P$ =10ms, Half Sine Wave
I <sub>FSM</sub>	Non-Repetitive Peak Forward Surge Current	236 212	A	$T_c$ =25°C, $T_P$ =10ms, Half Sine Wave Tc=125°C, $T_P$ =10ms, Half Sine Wave
PD	Power Dissipation	211 70	w	T <sub>c</sub> =25°C Tc=125°C
T <sub>J,max</sub>	Operating Junction Temperature	175	°C	
T <sub>stg</sub>	Storage Temperature Range	-55 to 175	°C	

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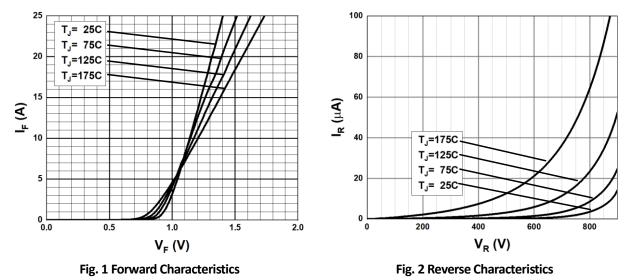
## **Thermal characteristics**

Symbol	Parameter	Min.	Тур.	Max.	Unit
R <sub>thJC</sub>	Thermal Resistance		0.71		°C/W

#### **Electrical Characteristics**

Symbol Parameter	Value		11	Test Conditions		
	Min.	Тур.	Max.	Unit	Test Conditions	
V <sub>DC</sub>	DC Blocking Voltage	650			V	I <sub>R</sub> =500μΑ, Τ <sub>J</sub> =25°C
V	V <sub>F</sub> Forward Voltage		1.45	1.7	V	I <sub>F</sub> =25A, T <sub>J</sub> =25°C
VF			1.75	2.0		I <sub>F</sub> =25A, T <sub>J</sub> =175°C
	I <sub>R</sub> Reverse Current 2 50 μΑ 50 300		V <sub>R</sub> =650V, T <sub>J</sub> =25°C			
IR			50	300	μΑ	V <sub>R</sub> =650V, T <sub>J</sub> =175°C
0			60			I <sub>F</sub> =25A, dI/dt=600A/μs
Q <sub>C</sub> Total Capacitive Charge		68		nC	T <sub>J</sub> =25°C, V <sub>R</sub> =400V	
			796			V <sub>R</sub> =1V, T <sub>J</sub> =25°C, f=1 MHz
С	Total Capacitance		157		pF	V <sub>R</sub> =200V, T <sub>J</sub> =25°C, f=1 MHz
			138			V <sub>R</sub> =400V, T <sub>J</sub> =25°C, f=1 MHz

# **Typical Performance**



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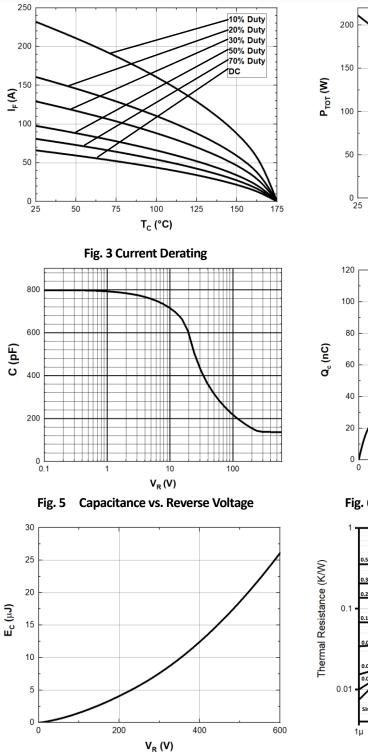


Fig. 7 Capacitance stored Energy

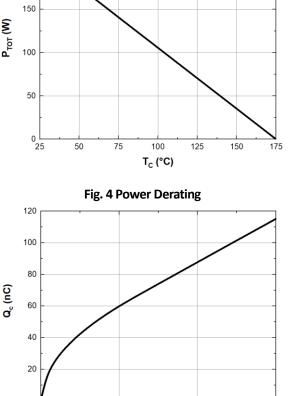


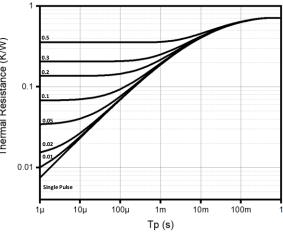
Fig. 6 Recovery Charge vs. Reverse Voltage

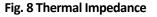
V<sub>R</sub> (V)

400

600

200



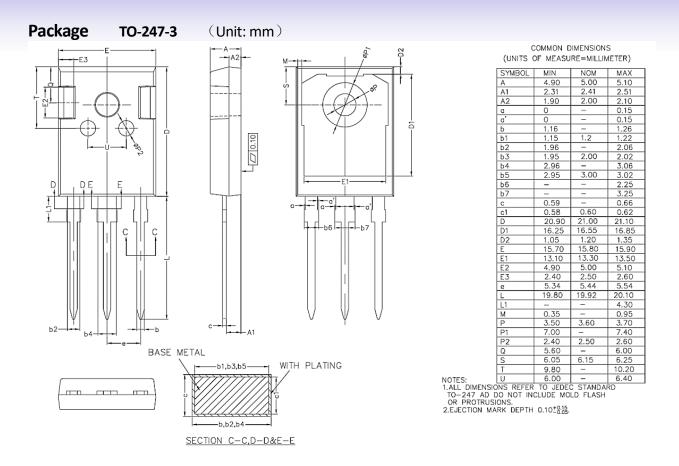


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